

OVERVIEW

The 5062 series are 2.5V/3.3V operation, HCSL output oscillator ICs. They support 100MHz to 175MHz 3rd overtone oscillation and 25MHz to 175MHz fundamental oscillation. They employ oscillator circuit appropriate for miniature 3rd overtone crystal, making these devices ideal for crystal oscillator modules of miniature package. The 5062 series can be used to construct wide frequency range HCSL output oscillators and low drive level by regulator drive of the oscillator circuit.

FEATURES

- Operating supply voltage range: 2.25 to 3.63V
- Recommended oscillation frequency range (varies with version)
 25MHz to 175MHz fundamental oscillation
 100MHz to 175MHz 3rd overtone oscillation
- -40 to +85°C operating temperature range
- HCSL output

- Oscillation capacitors C_G, C_D built-in
- Standby function
 High impedance in standby mode, oscillator stops
- Power-saving pull-up resistor built-in (OE pin)
- Wafer form (WF5062xx)
- Chip form (CF5062xx)

SERIES CONFIGURATION

Oscillation mode	Recommended oscillation frequency range*1 [MHz]	C ₀ cancellation circuit	Recommended C ₀ value ^{*2} [pF]	Version name ^{*3}
fundamental	25 to 100	No	to 1.5	(5062L6)
Tundamentai	100 to 175		$(\text{to } 2.0)^{*4}$	(5062M6)
3rd overtone	100 to 140	Voc	1.0 to 2.0	5062D6
fundamental	140 to 175	Yes	$(0.8 \text{ to } 2.5)^{*4}$	5062E6

^{*1.} The oscillation frequency is a yardstick value derived from the crystal used for Seiko NPC characteristics authentication. However, the oscillation frequency range is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

ORDERING INFORMATION

Device	Package	Version Name		
WF5062xx-3	Wafer form	WF5062□□-3 Form WF: Wafer form CF: Chip(Die) form Output frequency 6: f ₀		
CF5062xx-3	Chip form	Oscillation frequency L: 25 to 100MHz M: 100 to 175Hz D: 100 to 140MHz E: 140 to 175MHz		

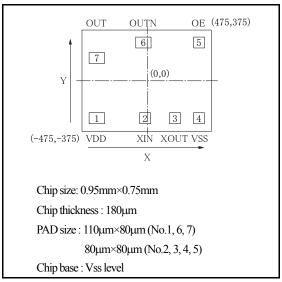
^{*2.} The oscillator circuit is optimized for 5032 to 3225 size crystal. In use of 7050 size crystal with large C₀ value, because the risk that oscillation margin is insufficient increases, it must be carefully evaluated.

^{*3.} The version name in parentheses is being developed.

^{*4.} Values in () are full range values. If using these ranges, careful evaluation is recommended before implementation.

PAD LAYOUT

(Unit: µm)



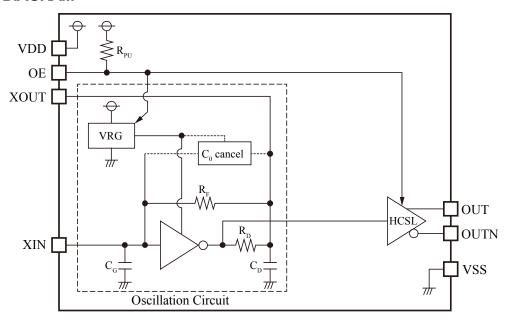
[·] Coordinates at the chip center are (0,0).

PIN DESCRIPTION and PAD COORDINATES

Nie	No. Die	I/O*1	Proposition	PAD coordinates [µm]		
No.	Pin	1/0	Function	X	Y	
1	VDD	-	(+) supply voltage	-363.7	-283.5	
2	XIN	I	Crystal connection pins	-11.7	-283.5	
3	XOUT	О	Crystal is connected between XIN and XOUT.	208.2	-283.5	
4	VSS	-	(-) ground	383.5	-283.5	
5	OE	I	Input pin controlled output state (oscillator stops when Low), Power-saving pull-up resistor built-in	383.5	283.5	
6	OUTN	О	HCSL output pin (Inverting output)	-29.1	283.5	
7	OUT	О	HCSL output pin (Non-inverting output)	-368.5	168.2	

^{*1.} I: Input pin O: Output pin

BLOCK DIAGRAM



SPECIFICATIONS

Absolute Maximum Ratings

Vss=0V

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range*1	V_{DD}	Between VDD and VSS	-0.3 to +4.0	V
Input voltage range*1*2	V_{IN}	Input pins	-0.3 to VDD+0.3	V
Output voltage range*1*2	V _{OUT}	Output pins	-0.3 to VDD+0.3	V
Junction temperature*3	T_j		+125	°C
Storage temperature range*4	T_{STG}	Chip form, Wafer form	-55 to +125	°C

^{*1.} This parameter rating is the values that must never exceed even for a moment. This product may suffer breakdown if this parameter rating is exceeded. Operation and characteristics are guaranteed only when the product is operated at recommended operating conditions.

Recommended Operating Conditions

Vss=0V

Parameter	Symbol	Condition	MIN	ТҮР	MAX	Unit
		5062L6	(25)		(100)	
Oscillator frequency*1	2	5062M6	100		175	MII-
Oscillator frequency	f_0	5062D6	100		140	MHz
		5062E6	140		175	
		5062L6	(25)		(100)	
O to A Community		5062M6	100		175	MHz
Output frequency	$f_{ m OUT}$	5062D6	100		140	
		5062E6	140		175	
Operating supply voltage	V_{DD}	Between VDD and VSS*2	2.25		3.63	V
Input voltage	$V_{\rm IN}$	Input pins	0		$V_{ m DD}$	V
Operating temperature	Ta		-40		+85	°C
Output load	R_{L}	OUT pin, OUTN pin, Terminated to V_{SS}	49.5		50.5	Ω

Values in parentheses () are temporary.

Note. Since it may influence the reliability if it is used out of range of recommended operating conditions, this product should be used within this range.

^{*2.} V_{DD} is a V_{DD} value of recommended operating conditions.

^{*3.} Do not exceed the absolute maximum ratings. If they are exceeded, a characteristic and reliability will be degraded.

^{*4.} When stored in nitrogen or vacuum atmosphere applied to IC itself only (excluding packaging materials).

^{*1.} The oscillation frequency is a yardstick value derived from the crystal used for Seiko NPC characteristics authentication. However, the oscillation frequency range is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

^{*2.} Mount a ceramic chip capacitor that is larger than 0.01µF proximal to IC (within approximately 3mm) between VDD and VSS in order to obtain stable operation of 5062 series. Furthermore, the better characteristic can be obtained by connecting the bypass capacitor of about 10µF. In addition, the wiring pattern between IC and capacitor should be as wide as possible.

Electrical Characteristics DC Characteristics

 V_{DD} =2.25 to 3.63V, V_{SS} =0V, T_a = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Conditions		MIN	ТҮР	MAX	Unit	
Current consumption	I _{DDL} _3.3V	Measurement circuit 1, OE=Open	$V_{DD}=3.3V$		(31.0)	(39.0)	A	
(L6 ver.)	I _{DDL} _2.5V	f ₀ =100MHz	V _{DD} =2.5V		(28.0)	(35.0)	mA	
Current consumption	I _{DDM} _3.3V	3V Measurement circuit 1, OE=Open V _{DD}			35.0	45.0	m A	
(M6 ver.)	I _{DDM} _2.5V	f ₀ =156.25MHz	V _{DD} =2.5V		31.0	41.0	mA	
Current consumption	I _{DDD} _3.3V	Measurement circuit 1, OE=Open	V _{DD} =3.3V		39.0	49.0	m A	
(D6 ver.)	I _{DDD} _2.5V	f ₀ =125MHz	V _{DD} =2.5V		35.5	45.5	5 mA	
Current consumption	I _{DDE} _3.3V	Measurement circuit 1, OE=Open	V _{DD} =3.3V		40.0	50.0	mA	
(E6 ver.)	I _{DDE} _2.5V	f ₀ =156.25MHz	V _{DD} =2.5V		36.5	46.5	ША	
Standby current	I_{STB}	Measurement circuit 1, OE=Low				15	μΑ	
High-level output voltage	V_{OH}	Measurement circuit 2		0.66		0.85	V	
Low-level output voltage	V _{OL}	OUT/OUTN pin		-0.15		0.15	V	
Output leakage current	I_Z	Measurement circuit 3, OE=Low, O	UT/OUTN pin			10	μА	
High-level input voltage	$V_{ m IH}$	Measurement circuit 1, OE pin	Measurement circuit 1, OE pin				V	
Low-level input voltage	V_{IL}	Measurement circuit 1, OE pin				$0.3V_{DD}$	V	
OE pin	R _{PU1}	Measurement circuit 1		0.2	1	8	ΜΩ	
pull-up resistance	R _{PU2}	Measurement circuit 1		30	70	150	kΩ	
Oscillator feedback resistance (L6 ver.)	R_{fL}			50	100	200	kΩ	
Oscillator feedback resistance (M6 ver.)	R_{fM}			50	100	200	kΩ	
Oscillator feedback resistance (D6 ver.)	R_{fD}			1.1	2.2	3.3	kΩ	
Oscillator feedback resistance (E6 ver.)	$R_{ m fE}$			1.1	2.2	3.3	kΩ	
Oscillator capacitance	C_{GL}	Design value (a monitor pattern on a v	vafer is tested),	9.6	12.0	14.4	ъE	
(L6 ver.)	C_{DL}	Excluding parasitic capacitance.		11.2	14.0	16.8	pF	
Oscillator capacitance	C_{GM}	Design value (a monitor pattern on a wafer is tested),		1.6	2.0	2.4	рF	
(M6 ver.)	C_{DM}	Excluding parasitic capacitance.		1.6	2.0	2.4	hr.	
Oscillator capacitance	C_{GD}	Design value (a monitor pattern on a v	vafer is tested),	1.6	2.0	2.4	pF	
(D6 ver.)	C_{DD}	Excluding parasitic capacitance.		1.6	2.0	2.4	pr	
Oscillator capacitance	C_{GE}	Design value (a monitor pattern on a v	vafer is tested),	0.8	1.0	1.2	pF	
(E6 ver.)	C_{DE}	Excluding parasitic capacitance.		0.8	1.0	1.2	þr.	

Values in parentheses () are temporary.

AC Characteristics

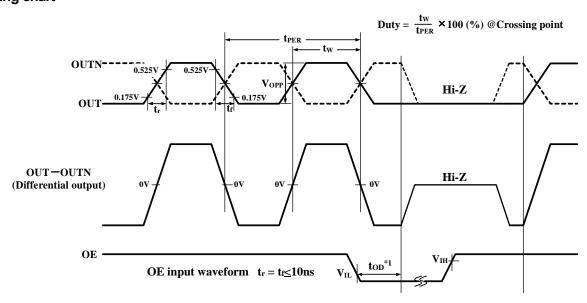
 V_{DD} = 2.25 to 3.63 V, V_{SS} = 0 V, T_a = -40 to +85 °C unless otherwise noted

Parameter	Symbol	Conditions		MIN	ТҮР	MAX	Unit
Output duty cycle	Duty	Measurement circuit 4 Measured at differential output signal 0V (crossing point)		45		55	%
Output swing	V_{OPP}	Measurement circuit 4, single-ended	output signal	0.4			V
Output rise time	Measurement circuit 4 t _r Measured at 0.175V to 0 single-ended output signa		C _L =0pF (no load)		200	400	
		single-ended output signal	$C_L=2pF^{*1}$		250	500	ps
Output fall time	t_{f}	Measurement circuit 4 Measured at 0.525V to 0.175V	C _L =0pF (no load)		200	400	n c
		single-ended output signal	$C_L=2pF^{*1}$		250	500	ps
	t _{OD}	Measurement circuit 5					
Output disable time		Time to becoming output Hi-Z at OE(fall)= $V_{\rm IL}$				200	ns
		(Refer to the timing chart for details.)					

^{*1.} The parasitic capacitance such as the evaluation boards and packages is included in external load C_L.

Note. The above values are measured by using Seiko NPC standard crystal and jig for evaluation. It must be carefully evaluated so that the values can vary due to crystal characteristics, parasitic component of a mount board and a package.

Timing chart



*1. The OUT/OUTN output goes high impedance after the OE is fallen and then the output disable time " t_{OD} " has elapsed. The output signal is pulled down to V_{SS} by load resistance.

Figure 1.Timing chart

FUNCTIONAL DESCRIPTION

OE Function

When OE goes Low, OUT/OUTN output is stopped and becomes high impedance.

OE	OUT/OUTN	Oscillator
High or Open	\mathbf{f}_0	Operating
Low	Hi-Z	Stopped

Power Saving Pull-up Resistor

The OE pin pull-up resistance changes its value to R_{PU1} or R_{PU2} in response to the input level (High or Low).

When OE is tied to Low level, the pull-up resistance becomes large (R_{PU1}) , thus reducing the current consumed by the resistance. When OE is left open circuit or tied to High level, the pull-up resistance becomes small (R_{PU2}) , thus internal circuit of OE becomes High level. Consequently, the IC is less susceptible to the effects of noise, helping to avoid problems such as the output stopping suddenly.

Oscillation Detection Function

The 5062 series have an oscillation detection circuit.

The oscillation detection circuit disables the output until crystal oscillation becomes stable when oscillation circuit starts up. This function avoids the abnormal oscillation in the initial power up and in a reactivation by OE.

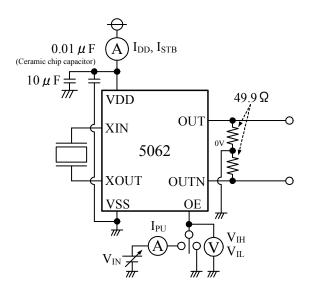
C₀ cancellation circuit

Oscillation circuit with a built-in C_0 cancellation circuit provides a fixed compensation amount to cancel the effect of the crystal C_0 . It reduces the C_0 parameter in the equivalent circuit, reducing the shallow negative resistance for increasing values of C_0 .

This cancellation circuit makes it easier to maintain the oscillation margin.

MEASUREMENT CIRCUITS MEASUREMENT CIRCUIT 1

 $Measurement\ Parameter:\ I_{DD},\ I_{STB},\ V_{IH},\ V_{IL},\ R_{PU1},\ R_{PU2}$

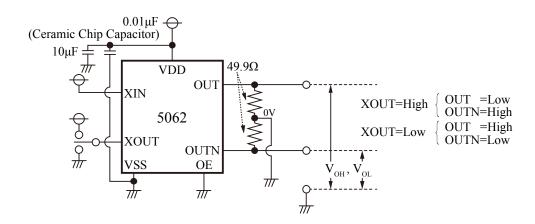


$$\begin{split} R_{PU1} \; &= \; \frac{V_{DD}}{I_{PU}} \qquad \qquad (V_{IN} = 0V) \\ R_{PU2} \; &= \; \frac{V_{DD} - 0.7 V_{DD}}{I_{PU}} \; (V_{IN} = 0.7 V_{DD}) \end{split}$$

 V_{IH} : $V_{SS}{\to}V_{DD}$ voltage that changes output state V_{IL} : $V_{DD}{\to}V_{SS}$ voltage that changes output state

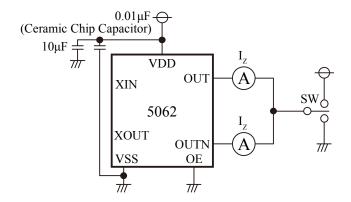
MEASUREMENT CIRCUIT 2

Measurement Parameter: V_{OH} , V_{OL}



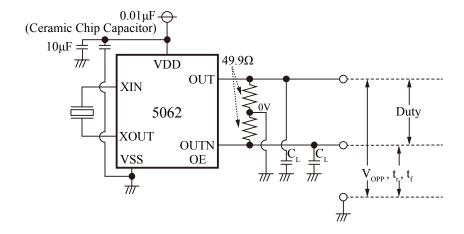
MEASUREMENT CIRCUIT 3

Measurement Parameters: I_Z



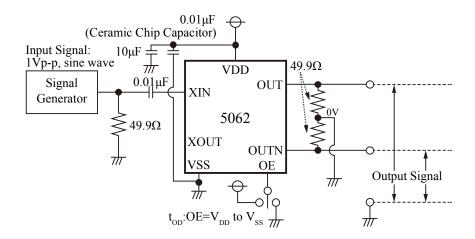
MEASUREMENT CIRCUIT 4

Measurement Parameter: Duty, V_{OPP} , t_{r} , t_{f}



MEASUREMENT CIRCUIT 5

Measurement Parameter: t_{OD}



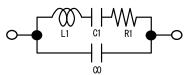
REFERENCE DATA

The following characteristics are measured using the crystal below. Note that the characteristics will vary with the crystal used.

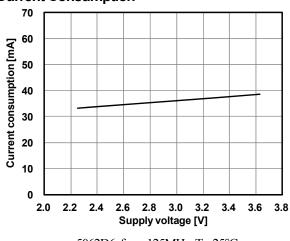
Crystal used for measurement (3rd overtone)

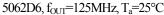
Parameter	f ₀ =125.00MHz	f ₀ =156.25MHz
C ₀ (pF)	1.8	1.2
$R_1(\Omega)$	35	60

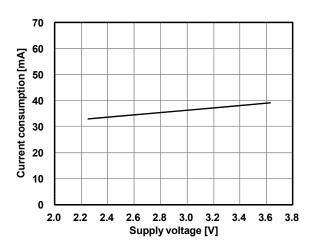




Current Consumption



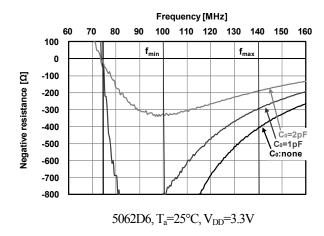


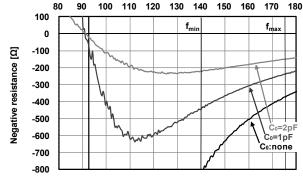


5062E6, $f_{OUI}=156.25MHz$, $T_a=25$ °C

Frequency [MHz]

Negative Resistance



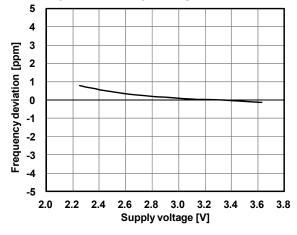


5062E6, T_a=25°C, V_{DD}=3.3V

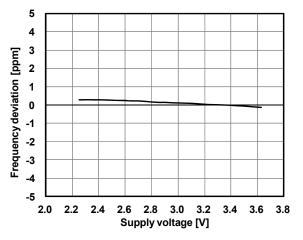
The figures show the measurement result of the crystal equivalent circuit C_0 capacitance, connected between the XIN and XOUT pins. They were performed with Agilent 4396B using the NPC test jig.

They may vary in a measurement jig, and measurement environment.

Frequency Deviation by Voltage

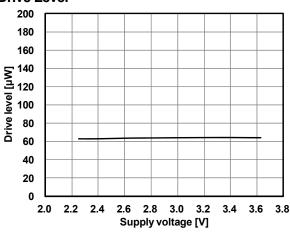


5062D6, $f_{OUT}=125MHz$, $T_a=25$ °C, 3.3V std.

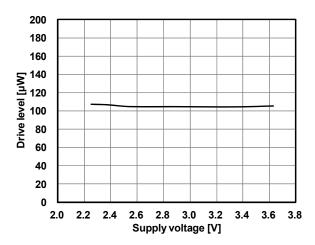


5062E6, $f_{OUT}=156.25MHz$, $T_a=25$ °C, 3.3V std.

Drive Level

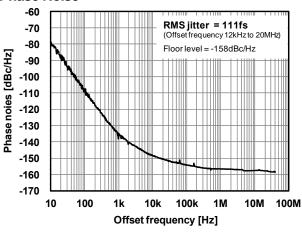


5062D6, $f_{OUT}=125MHz$, $T_a=25$ °C

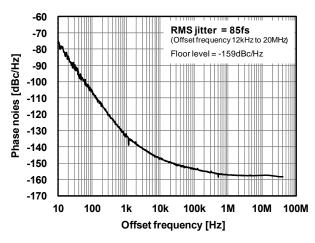


5062E6, $f_{OUT}=156.25MHz$, $T_a=25$ °C

Phase Noise



5062D6, f_{OUT}=125MHz, T_a=25°C, V_{DD}=3.3V

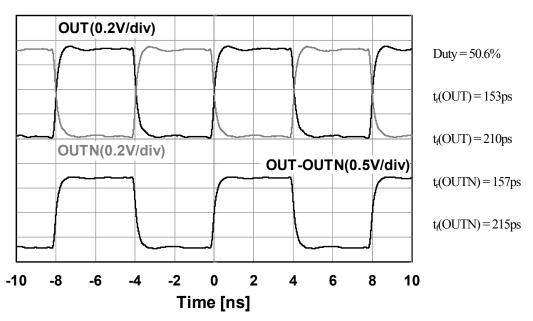


5062E6, $f_{OUT}=156.25MHz$, $T_a=25$ °C, $V_{DD}=3.3V$

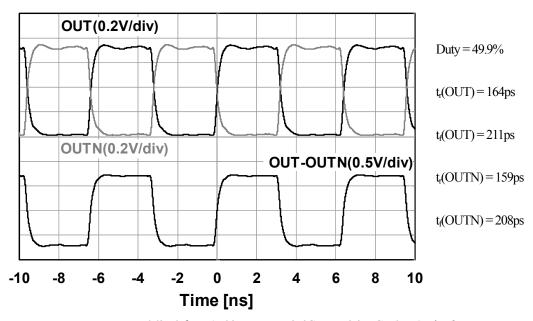
Measurement instrument: Agilent E5052B Signal Source Analyzer

Output Waveform

• Output load: no load (C_L=0pF)

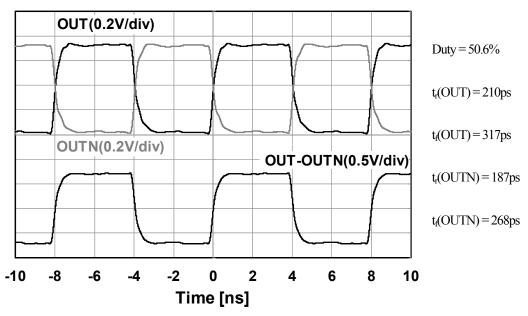


5062D6, f_{OUT} =125MHz, T_a =25°C, V_{DD} =3.3V, C_L =0pF (no load)

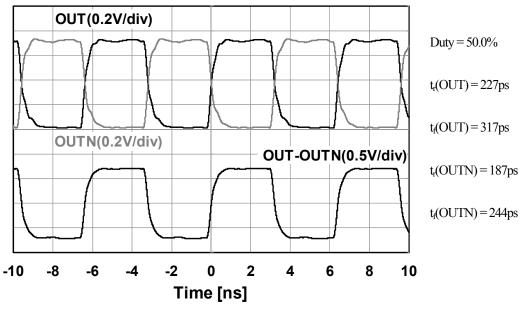


5062E6, f_{OUT} =156.25MHz, T_a =25°C, V_{DD} =3.3V, C_L =0pF (no load)

Output load: C_L=2pF
 Since output waveform may be influenced if load capacitance is added, it must be carefully evaluated.



 $5062D6, f_{OUT}=125MHz, T_a=25^{\circ}C, V_{DD}=3.3V, C_L=2pF$



5062E6, f_{OUI} =156.25MHz, T_a =25°C, V_{DD} =3.3V, C_L =2pF

Measurement equipment: Oscilloscope DSO80604B (Agilent)
Differential probe 1134A (Agilent)
Probe head E2675A (Agilent)

Please pay your attention to the following points at time of using the products shown in this document.

reliability as expected for use in general electronic and electrical equipment, such as personal equipment, machine tools and measurement equipment. The Products are not designed and manufactured to be used in any other special equipment requiring extremely high level of reliability and safety, such as aerospace equipment, nuclear power control equipment, medical equipment, transportation equipment, disaster prevention equipment, security equipment. The Products are not designed and manufactured to be used for the apparatus that exerts harmful influence on the human lives due to the defects, failure or malfunction of the Products. If you wish to use the Products in that apparatus, please contact our sales section in advance.

In the event that the Products are used in such apparatus without our prior approval, we assume no responsibility whatsoever for any

1. The products shown in this document (hereinafter "Products") are designed and manufactured to the generally accepted standards of

- In the event that the Products are used in such apparatus without our prior approval, we assume no responsibility whatsoever for any damages resulting from the use of that apparatus.
- 2. Seiko NPC reserves the right to change the specifications of the Products in order to improve the characteristics or reliability thereof.
- 3. The information described in this document is presented only as a guide for using the Products. No responsibility is assumed by us for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of the third parties. Then, we assume no responsibility whatsoever for any damages resulting from that infringements.
- 4. The constant of each circuit shown in this document is described as an example, and it is not guaranteed about its value of the mass production products.
- 5. In the case of that the Products in this document falls under the foreign exchange and foreign trade control law or other applicable laws and regulations, approval of the export to be based on those laws and regulations are necessary. Customers are requested appropriately take steps to obtain required permissions or approvals from appropriate government agencies.



SEIKO NPC CORPORATION

1-9-9, Hatchobori, Chuo-ku, Tokyo 104-0032, Japan Telephone: +81-3-5541-6501 Facsimile: +81-3-5541-6510 http://www.npc.co.jp/ Email:sales@npc.co.jp

ND13014-E-02 2015.1